

# 多重散乱法を用いた プラズモンロス計算の使用例

千葉大学

融合理工学府 先進理化学専攻 助教

二木かおり

17.09.25

$$\langle \psi_{\vec{k}}^- | \Delta | \phi_i \rangle \approx \sum_{\alpha} e^{-i\vec{k} \cdot \vec{R}_{\alpha}} \sum_{L_1, L_2} \sum_{A, L_3} Y_{L_1}(\hat{\mathbf{k}}) [(1 - \mathbf{X})^{-1}]_{L_1, L_2}^{\alpha, A} M_{L_2, L_3}^A$$

### 多重散乱理論 Multiple Scattering theory

Enable us to simulate the behavior of photoelectrons

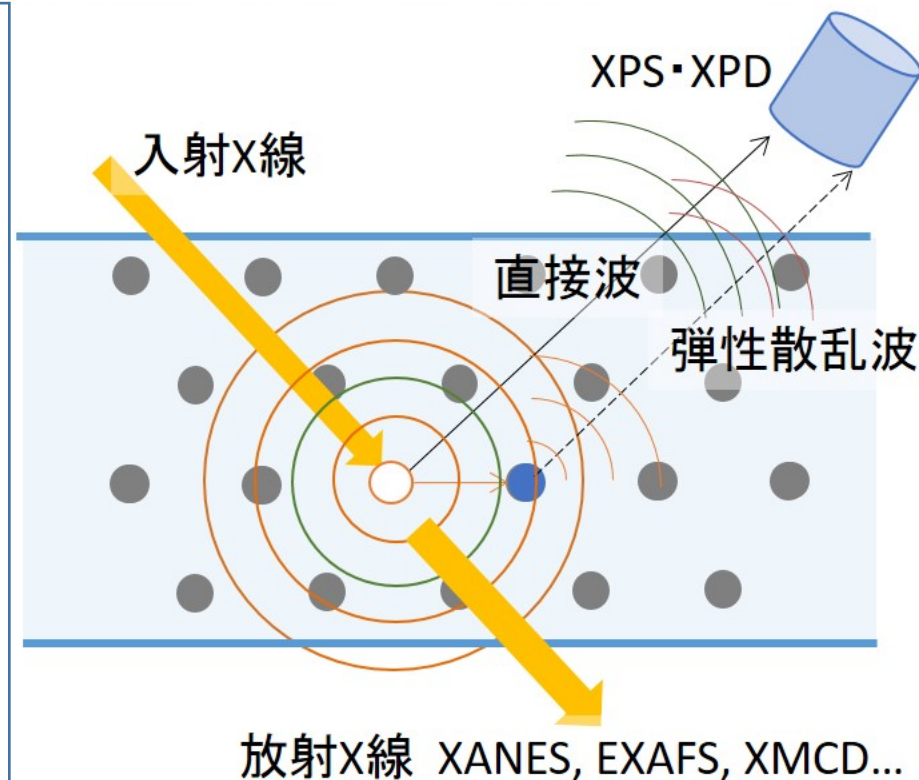
It appropriate for considering the

**unoccupied states = continuum state**

= the behavior of **photoelectron**

$$|\psi_{\vec{k}}^- \rangle = |\phi_{\vec{k}} \rangle + \frac{1}{E_k - H_0 - i0^+} V |\psi_{\vec{k}}^- \rangle$$

$$V(\vec{r}) = \sum_{\alpha} v_{\alpha} (|\vec{r} - \vec{R}_{\alpha}|)$$



Enable us to simulate the behavior of photoelectrons

## Multiple Scattering theory

Is appropriate for considering the **unoccupied states=continuum state**= the behavior of **photoelectron**

Partition the real space into atomic scattering regions

$$V(\vec{r}) = \sum_{\alpha} v_{\alpha} (|\vec{r} - \vec{R}_{\alpha}|)$$

Apply Lipmann-Schwinger Eq. for final state

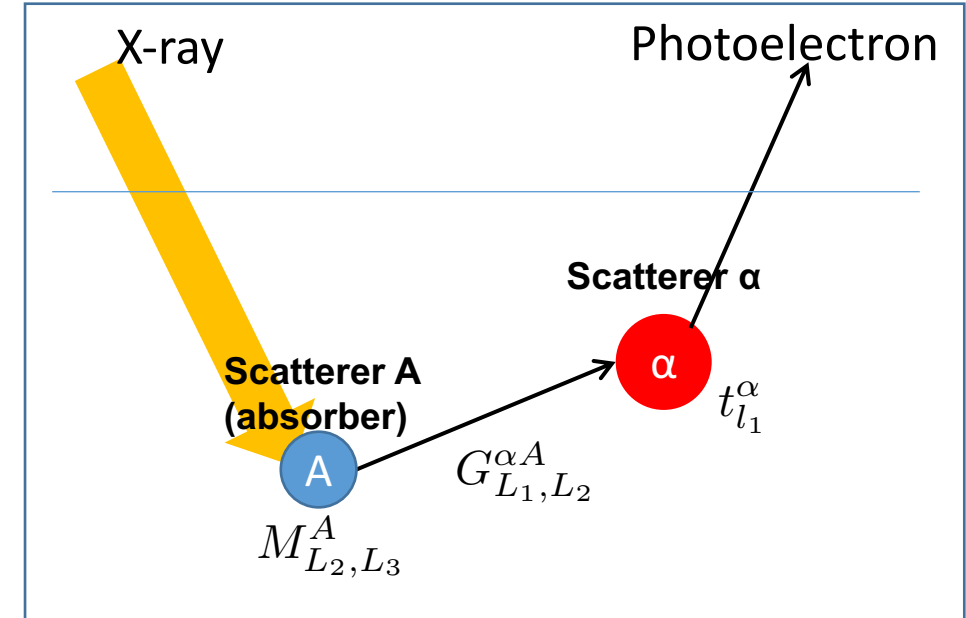
$$|\psi_{\vec{k}}^{-}\rangle = |\phi_{\vec{k}}\rangle + \frac{1}{E_k - H_0 - i0^+} V |\psi_{\vec{k}}^{-}\rangle$$

Scattering amplitude

$$\langle \psi_{\vec{k}}^{-} | \Delta | \phi_i \rangle \approx \sum_{\alpha} e^{-i\vec{k} \cdot \vec{R}_{\alpha}} \sum_{L_1, L_2} \sum_{A, L_3} Y_{L_1}(\hat{\mathbf{k}}) [(1 - X)^{-1}]_{L_1, L_2}^{\alpha, A} M_{L_2, L_3}^A$$

propagation / scattering

optical transition in atom A



Initial state WF

- Atomic WF
- Molecular Orbital ( Gaussian )

Potential

Atomic scattering

- Radial integral
- Phase shift

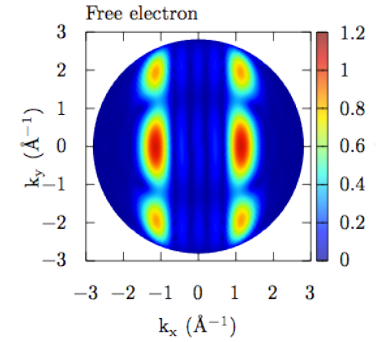
MS theory

Photoemission amplitude

Our lab...

Electronic state  
Adsorbing effects

Full potential Pentacene  
**ARPES**



Surface structure  
Magnetic anisotropy

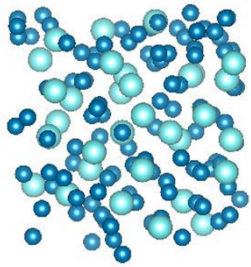
$\text{Fe}_2\text{O}_3$  surface

Multiple  
Scattering  
theory

To explore physical  
properties

科研費 若手B

**Plasmon loss**



Amorphous  
magnetic thin film

**EXAFS**  
**XMCD**

Heusler alloy systems  
Electrode of Li-ion battery

**XPS**

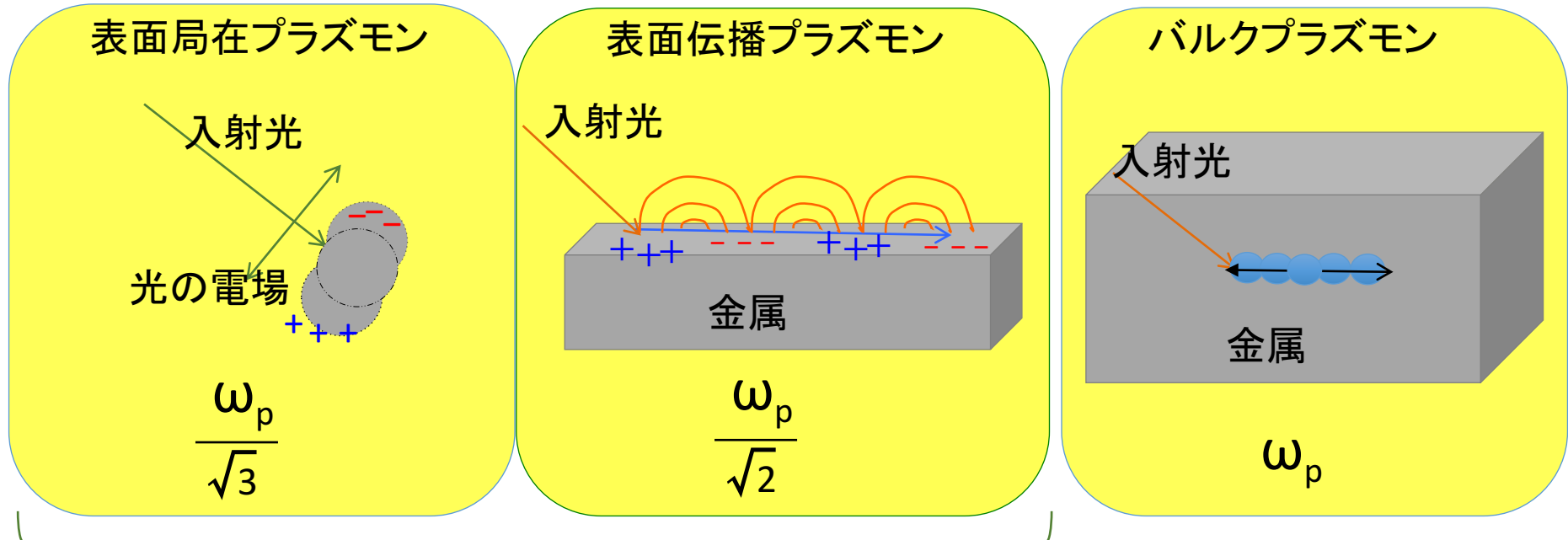
Metal  
Thin Film (Graphene...)  
Nano particles,

# Satellite peaks in XPS; plasmon loss peaks

1. Expressions for plasmon loss intensity  
which is called Quantum Landau formula.
2. Extension to other systems  
... graphene sheet and nano particles.

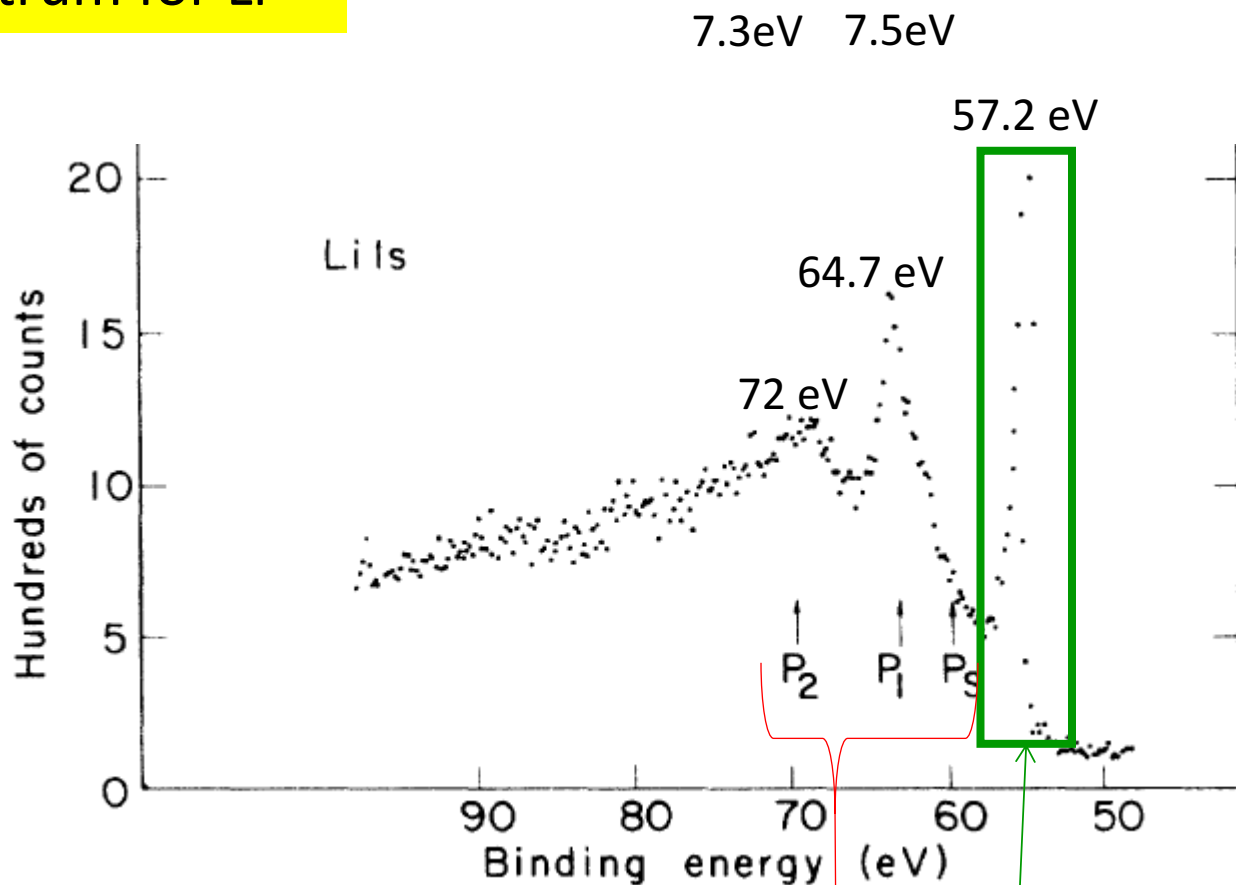
# プラズモン

固体物質中での自由電子の集団振動  
電荷分布のずれにより誘起される。  
物質固有の共鳴振動数 $\omega_p$ をもつ。



近接場光

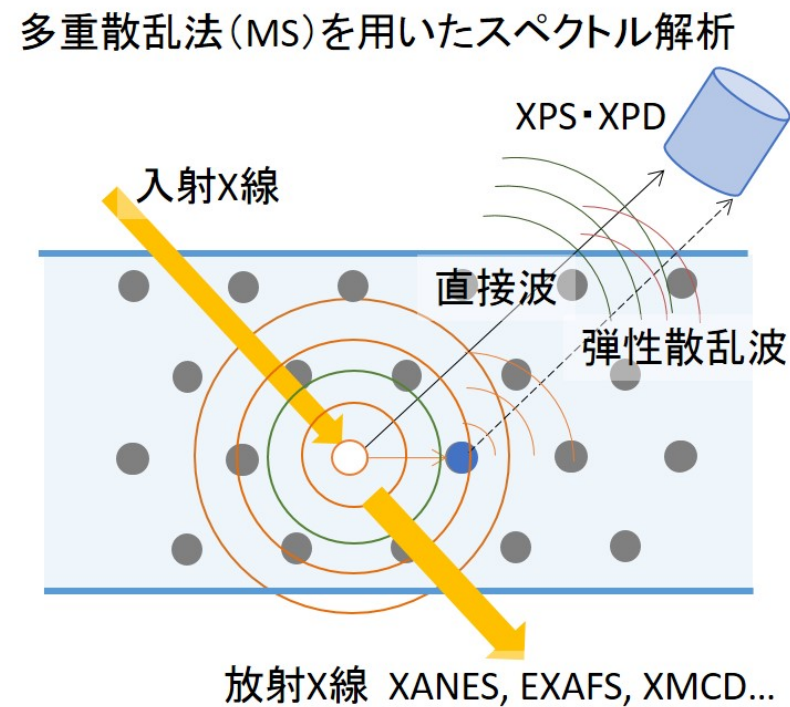
→ ナノフォトニクス・プラズモニクスへの応用



Plasmon loss Main peak

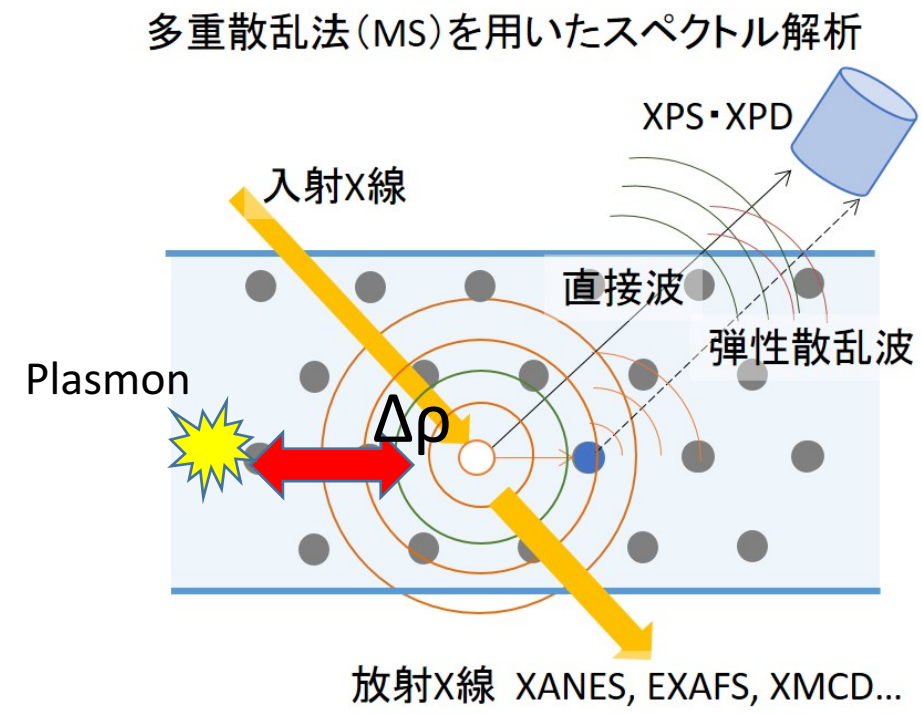
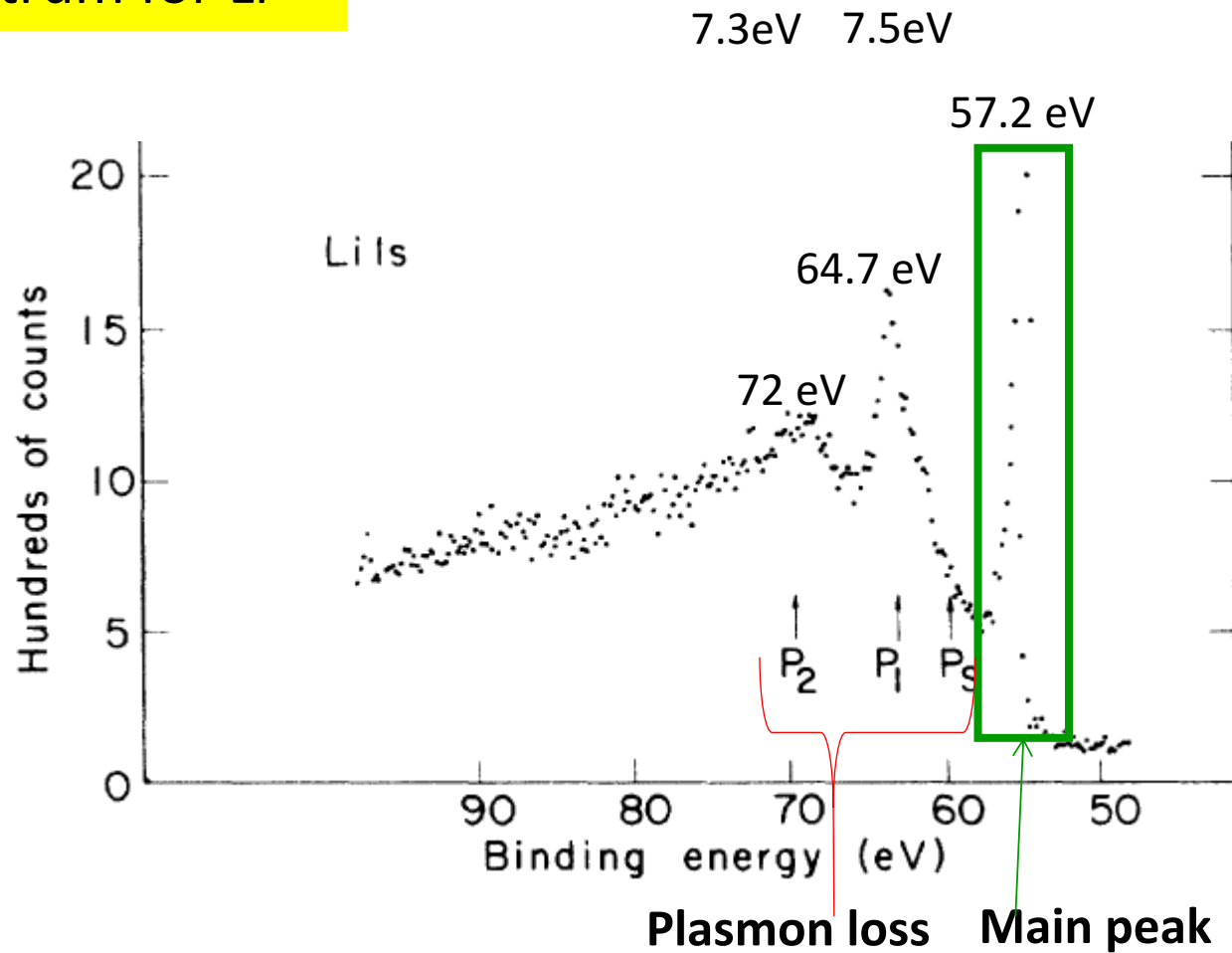
$$I(\mathbf{p}; \omega)_c^1 + \dots ??$$

$$I(\mathbf{p}; \omega)_c^0 = 2\pi \left| \langle f_p^- | \Delta | \phi_c \rangle S_0 \right|^2 \delta(E_0 + \omega - E_0^* - \varepsilon_p)$$



Plasmon is collective electron oscillation excited by  $\Delta\rho$ .

Plasmon loss peaks in XPS are observed due to excite the plasmon by photoelectron.



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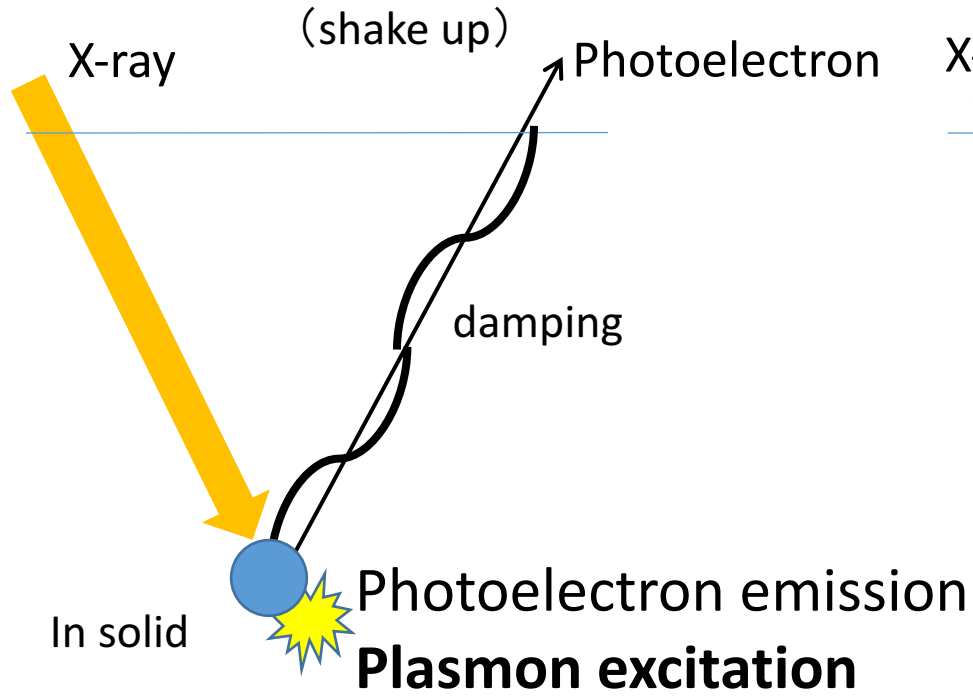
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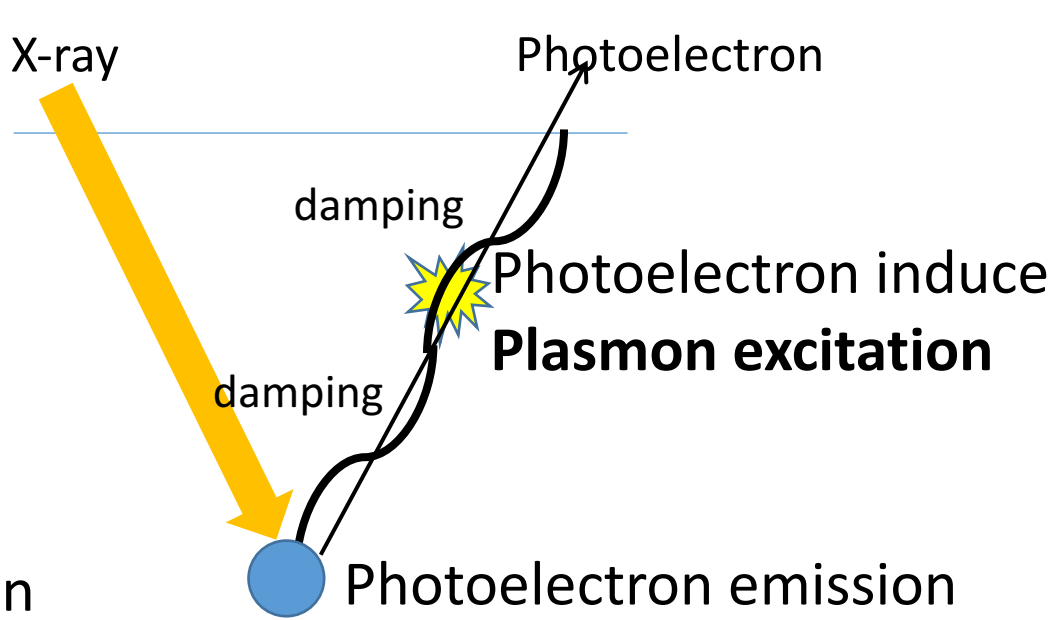


# Plasmon Losses in XPS

**Intrinsic plasmon**



**Extrinsic plasmon**



$$I(\mathbf{p}; \omega)^1 = 2\pi \sum_m \left[ \left\langle f_p^- \left| \Delta \left| \phi_c \right. \right. \right\rangle \left\langle m_v^* \left| 0_v^* \right. \right\rangle \right]_{\text{Int}} + \left[ \left\langle f_p^- \left| v_m g(\epsilon_p + \omega_m) \Delta \left| \phi_c \right. \right. \right\rangle e^{-\frac{a}{2}} \right]_{\text{Ext}}^2 \times \delta(E_0 + \omega - E_0^* - \omega_m - \epsilon_p)$$

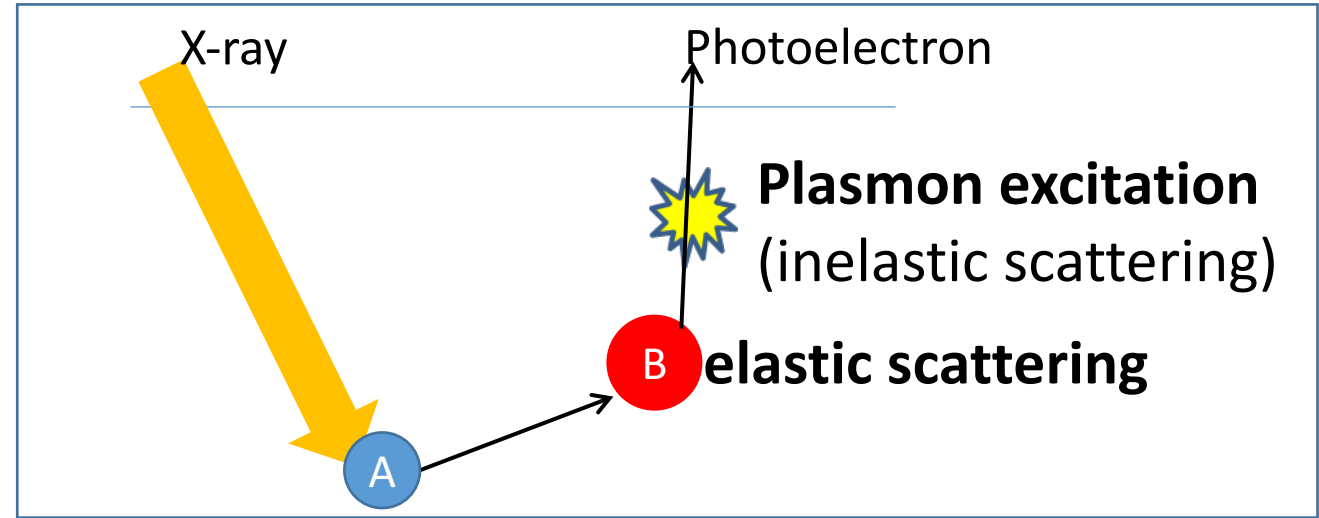
loss propagation

**干涉！！**

valence electrons  
note by no core

The fluctuation potential  $v_n(\mathbf{r}) = \int d\mathbf{r}' v(\mathbf{r} - \mathbf{r}') \langle n_v | \psi^\dagger(\mathbf{r}') \psi(\mathbf{r}') | 0_v \rangle.$

Take account into the elastic scattering during propagation for extrinsic term



$$\tau_{ext}(\mathbf{p}) = \langle f_{\mathbf{p}}^- | v_m g(\varepsilon_p + \omega_m) \Delta | \phi_c \rangle e^{-\frac{a}{2}} \langle \phi'_p | (1 + t g_0)$$

rewrite the T-matrix using the site-T matrix

$$= \langle \phi'_p | \left( 1 + t_A g_0 + \sum_{\substack{\alpha \neq A \\ \beta = A}} t_{\alpha} g_A + \sum_{\substack{\alpha \neq A \neq \beta \\ \gamma = A}} t_{\beta} g_0 t_{\alpha} g_A + \dots \right) v_m (g_A + \sum_{\beta \neq A} g_0 t_{\beta} g_A + \dots) \Delta | \phi_c \rangle e^{-\frac{a}{2}}$$

The effect of scattering

$$= e^{-\frac{a}{2}} \left\{ \langle \phi'_p | (1 + t_A g_0) v_m g_A \Delta | \phi_c \rangle + \langle \phi'_p | (1 + t_A g_0) v_m \sum_{B \neq A} g_0 t_B g_A \Delta | \phi_c \rangle + \dots \right.$$

Without elastic scatterings Single scattering by atom B

$$= \tau_m^{ex}(\mathbf{p}) \langle f_{\mathbf{p}}^- | \Delta | \phi_c \rangle$$

$$\tau_m^{ex}(\mathbf{p}) = (2\pi)^{3/2} \int dr f_{\mathbf{p}}^{-*}(r) v_m(r) g_0(r - \mathbf{R}_A; p'). \quad g_A = g_0 + g_0 t_A g_0$$

# Quantum Landau formula For lower calculation cost

$$I(\mathbf{p}; \omega)^1 = 2\pi \sum_m \left[ \underbrace{\langle f_{\mathbf{p}}^- | \Delta | \phi_c \rangle \langle m_v^* | 0_v^* \rangle}_{\text{Int}} + \underbrace{\langle f_{\mathbf{p}}^- | v_m g(\varepsilon_p + \omega_m) \Delta | \phi_c \rangle e^{-\frac{a}{2}}}_{\substack{\text{Ext} \\ \text{loss propagation}}} \right]^2 \times \delta(E_0 + \omega - E_0^* - \omega_m - \varepsilon_p)$$

光電子が  
固体中の原子に  
散乱される影響

Substitute  $\tau_m^{ex}(\mathbf{p}) \langle f_{\mathbf{p}}^- | \Delta | \phi_c \rangle S_0$

$$\tau_m(P) = \tau_m^{ex}(P) + \frac{S_m}{S_0} \quad \frac{\alpha(\varepsilon)}{\varepsilon} = \sum_m |\tau_m(P)|^2 \delta(\varepsilon - \omega_m) \quad \varepsilon = \omega + E_0 - E_0^* - \varepsilon_p$$

## Quantum Landau formula with full multiple scattering

◆ Single loss: spectrum of one plasmon excitation

$$I^1(\mathbf{p}, \omega) = \underbrace{\left| \langle f_{\mathbf{p}}^- | \Delta | \phi_c \rangle \right|^2}_{\text{Photo emission}} \underbrace{\frac{\alpha(\varepsilon)}{\varepsilon}}_{\substack{\text{Plasmon} \\ \text{Excitation}}} \exp \left[ \int_0^\infty d\varepsilon \frac{\alpha(\varepsilon)}{\varepsilon} \right]_{\text{nonlinearization}}$$

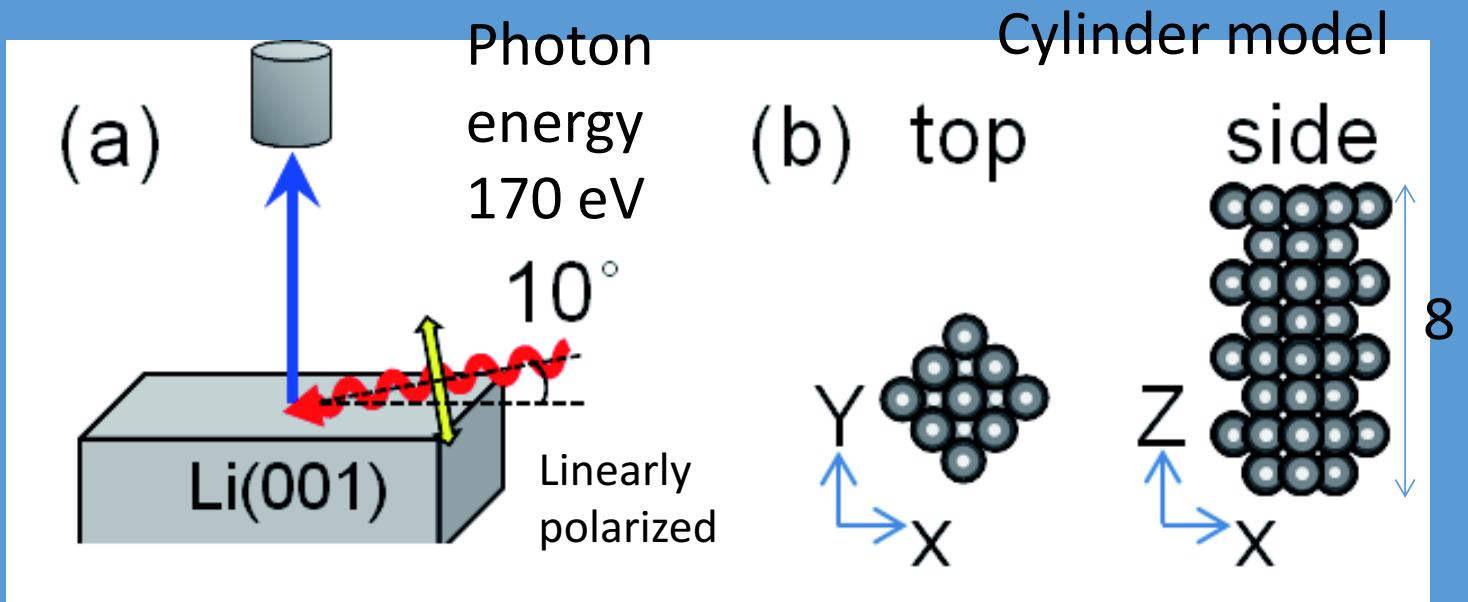
Peak height

Shape of  
loss function

## Purpose

We calculate single-plasmon loss features associated with Li 1s photoemission using the QLF that includes full multiple scatterings.

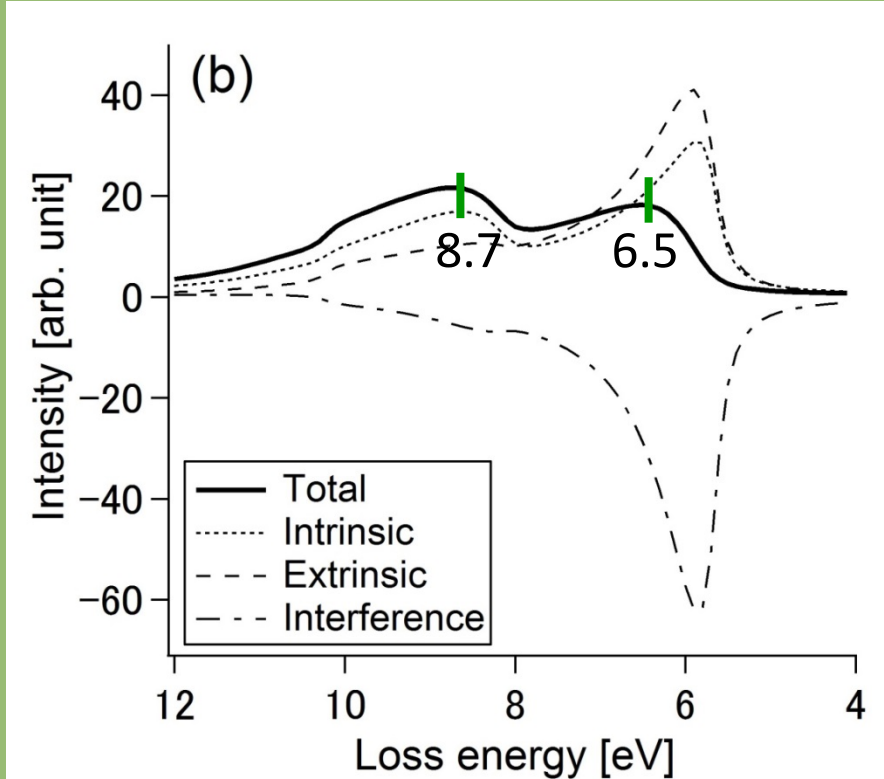
The schematic view of the calculation setup



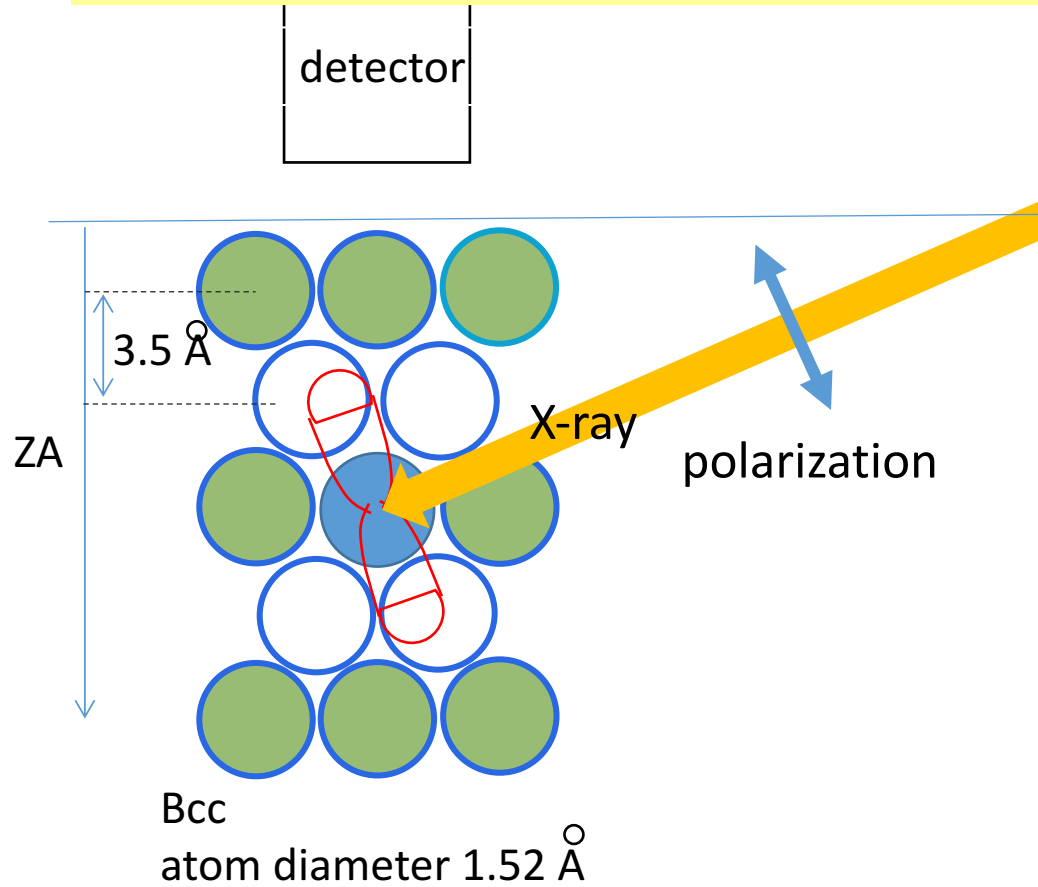
The energy of photoelectrons from Li 1s are about 100 eV.

Cylinder model contains 52 atoms.

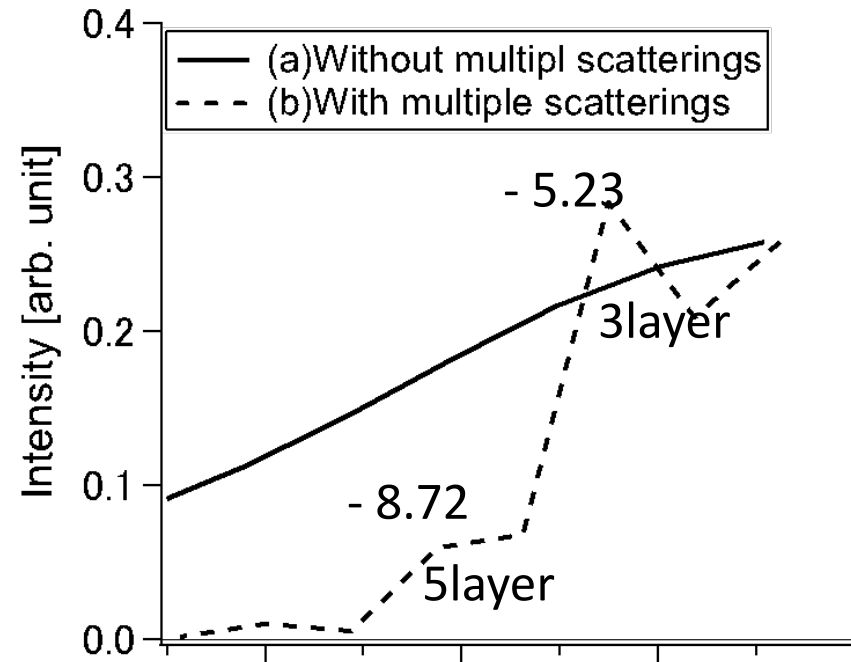
Calculation result



# Calculated single-plasmon loss intensities excited from Li 1s



## Depth profile of plasmon loss



Distance between the surface to emitter

3rd and 5th layer are also emphasized due to the defocusing effect.

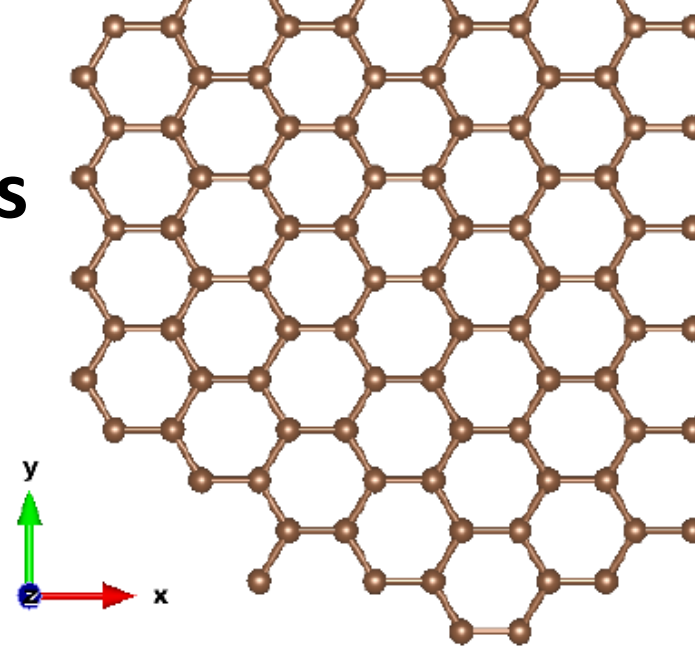
Photo electron emitted parallel to polarization from Li 1s is effected by defocusing effect.

**Info from only calculation!!**

Li is light atom,  
However we can't neglect the effect of elastic scattering.

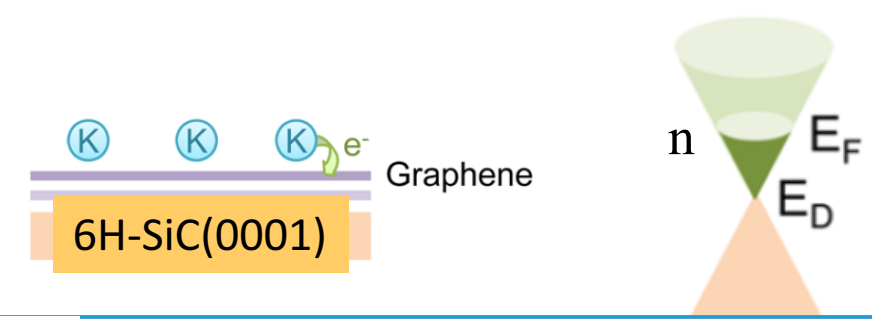
Expansion to other systems...低次元電子系

For metamaterials and photoelectronics devices



# Observation of the low energy $\Pi$ plasmon in a single layer graphene by charge doping using EELS

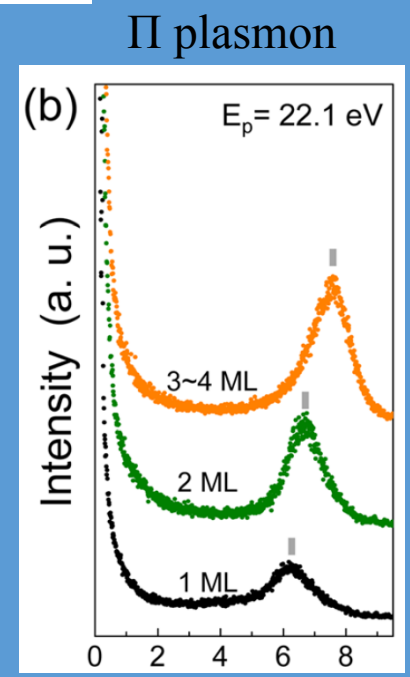
Control of the  $\Pi$  plasmon in a single layer graphene by charge doping  
 S. Y. Shin *et al.*, APPLIED PHYSICS LETTERS 99, 082110 (2011).



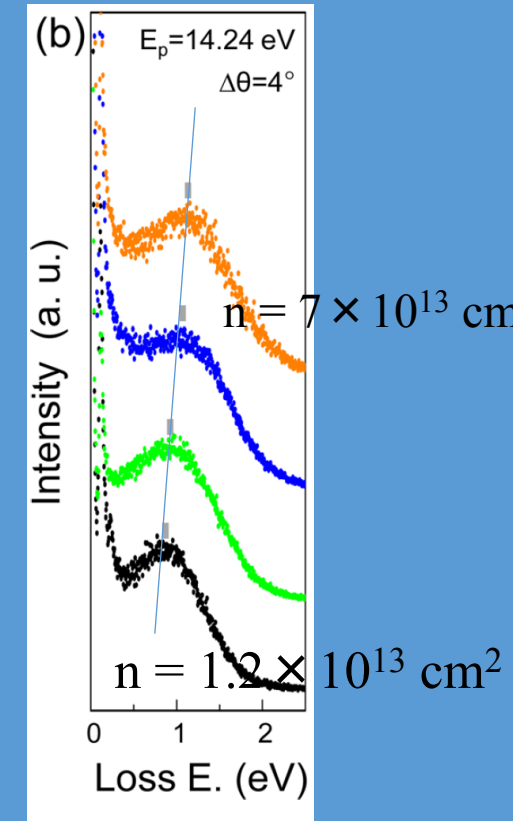
On a single layer graphene (SLG)

- They report a  $\Pi$  plasmon excitation  $n = 1.2 \times 10^{13} \text{ cm}^{-2}$  (naturally doped from the substrate).
- **They find a low-energy  $\Pi$  plasmon excitation** arising from doped electron density  $1.2 \times 10^{13} \text{ cm}^{-2}$  corresponding to 0.44 eV above the Dirac point ED (additional charge transfer from K to an SLG epitaxially grown on SiC).
- This low-energy plasmon arises from the collective excitation of electrons within the partially occupied  $\pi^*$  conduction band.

## EELS



## a low-energy $\Pi$ plasmon



$E_p$  is a primary electron beam energy,  
 $\Delta\Theta$  is an incident (scattered) angle.

# Observation of the $\Pi$ plasmon in a single layer graphene by charge doping using XPS

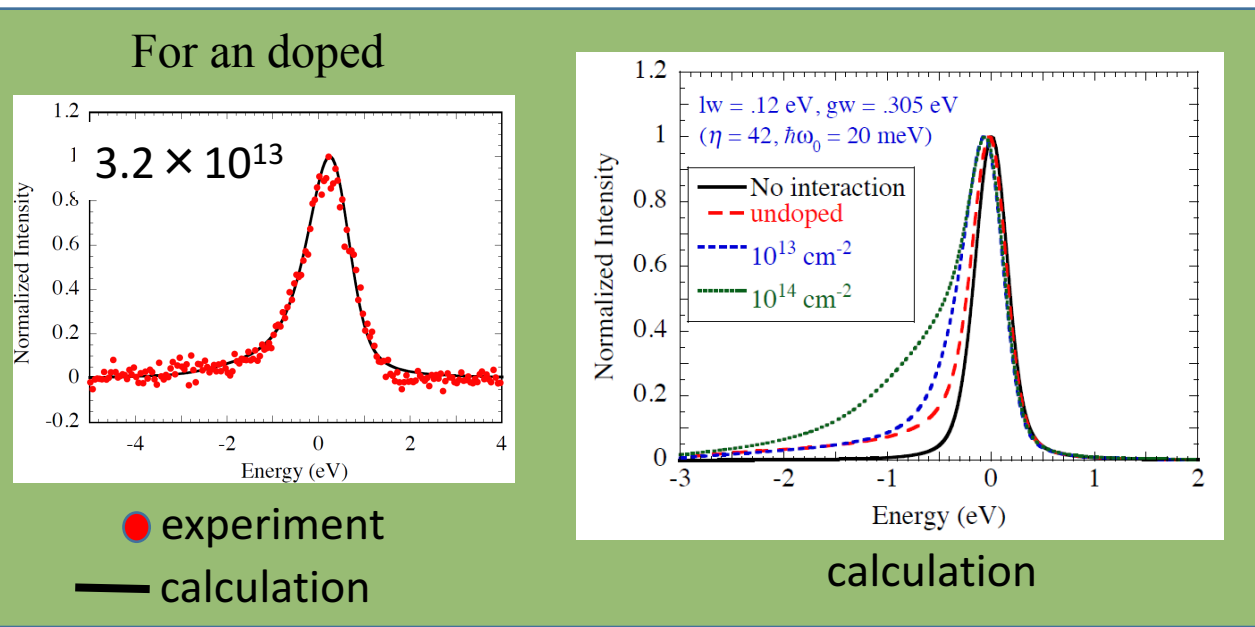
Core-level spectra from graphene  
 Bo E. Sernelius P R B (91), 4, 045402 (2015).

Experimental ( $\mu$ -XPS) C 1s core-level spectrum of a suspended single graphene sheet on a gold sheet using the photon energy 480 eV.

Theory of core-level spectra in x-ray photoemission of pristine and doped graphene

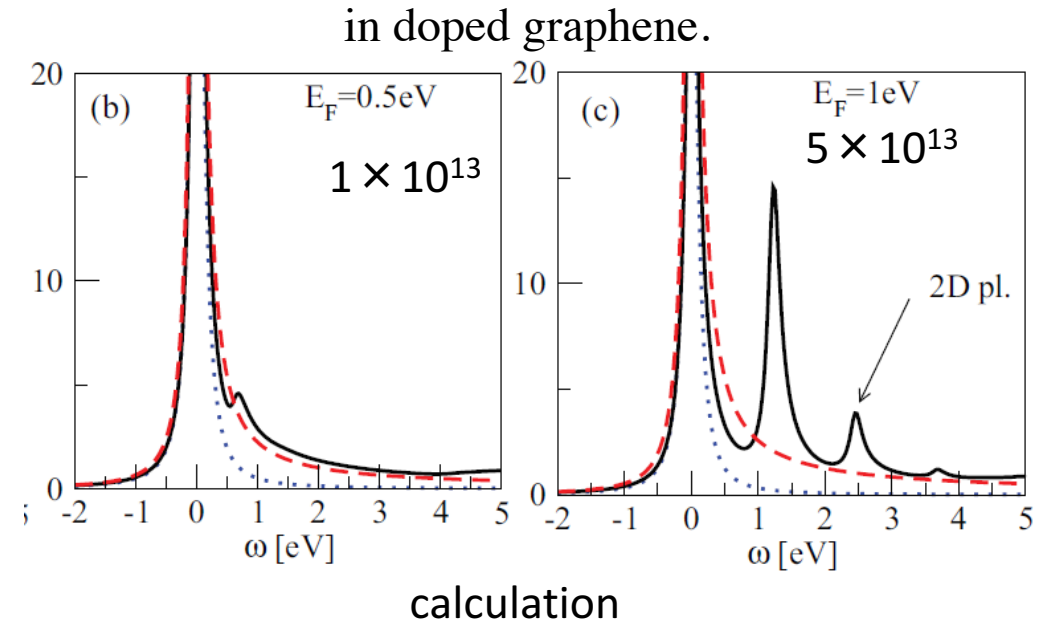
V. Despoja<sup>1,2,3,\*</sup> and M Šunjić<sup>1,2</sup>

They calculate singularity indices in pristine and doped graphene using dynamically screened Coulomb interaction



We can not see sharp a plasmon loss peak due to singularity even if increasing doping.

We want to extract a information about from singularity.  
 extent to electron-hole pair, excitation near fermi level....



We can see sharp plasmon loss peaks with doping.

P R B , 88, 245416 (2013).

Collaborate with Rennes uni. based on JASSO.



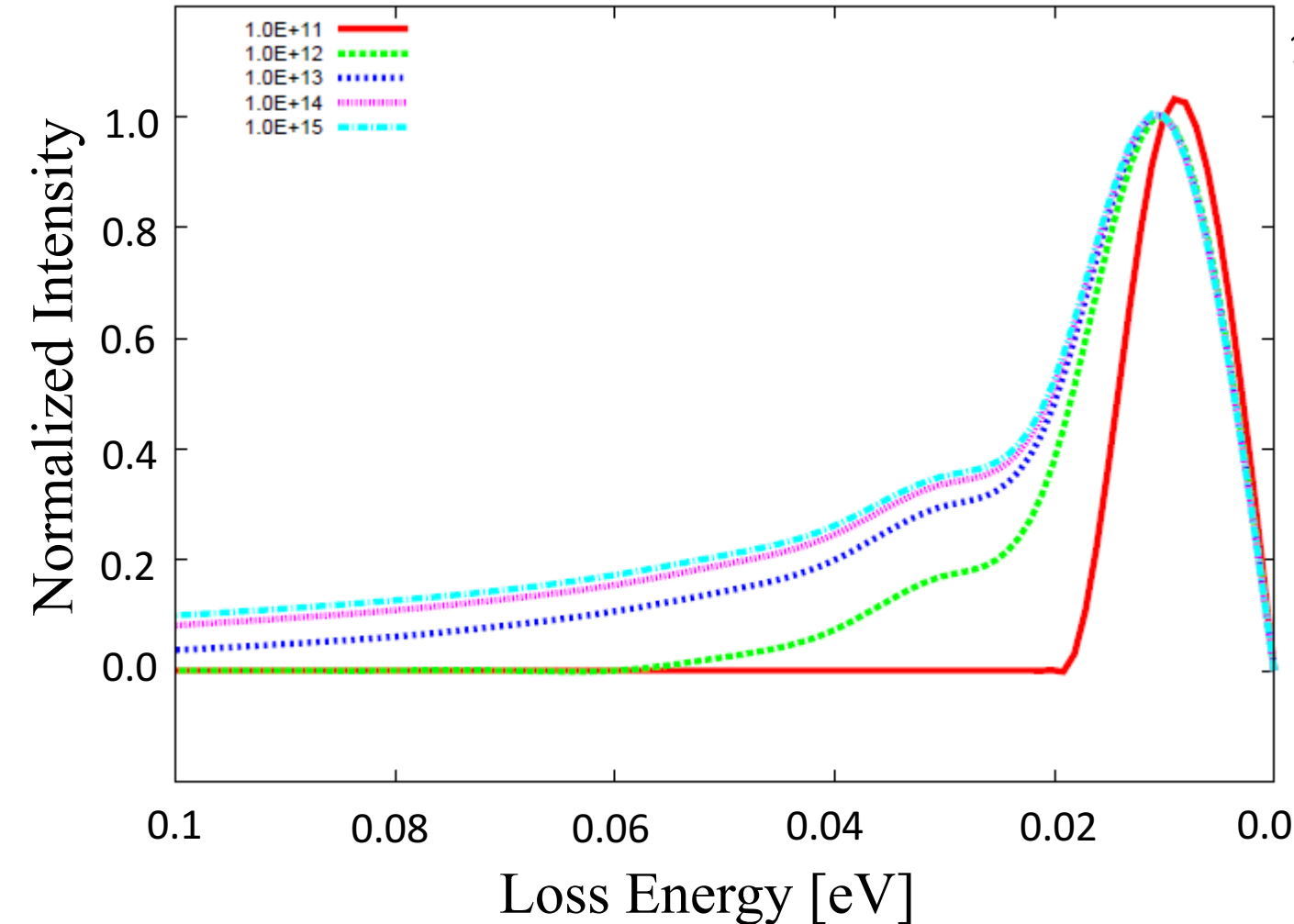
# ○キャリア密度依存性

・ $h\nu = 450$  eV条件

$n = 1.0 \times 10^{11}, 10^{12}, 10^{13}, 10^{14}, 10^{15} \text{ cm}^{-2}$   
の場合のそれぞれ計算

ピーク位置のシフトはほとんどない  
→密度依存性は現れない

密度が高いほど高ロスエネルギー側に  
裾の長いピークになる  
→キャリア密度がプラズモン分散に関与



# まとめ

量子ランダウ方程式からメインピークのサテライトピークである  
プラズモンロスピークが計算できる

単純金属、2次元電子系グラフェン、0次元電子系のナノ粒子などへの  
拡張が見込まれる